

TO-202 TRIDAC®

MAXIMUM RATINGS		SYMBOL	V _{DRM}	DEVICE NUMBERS			UNITS
Repetitive Peak Off-State Voltage (1) Gate Open, and T _J = 110° C		V _{DRM}	200 400 500 600	8TD24 8TD44 8TD54 8TD64	8TD26 8TD46 8TD56 8TD66	8TD28 8TD48 8TD58 8TD68	VOLT
RMS On-State Current at T _C = 80°C and Conduction Angle of 360°		I _{T(RMS)}		4.0	6.0	8.0	AMP
Peak Surge (Non-Repetitive) On-State Current, One-Cycle, at 50Hz or 60Hz		I _{TSM}		40	60	80	AMP
Peak Gate-Trigger Current for 3μsec. Max.		I _{GTM}		1.2	1.5	1.5	AMP
Storage Temperature Range		T _{stg}		-40 to +150			°C
Operating Temperature Range, T _J		T _{oper}		-40 to +110			°C
ELECTRICAL CHARACTERISTICS At Specified Case Temperature							
Peak Off-State Current, (1) Gate Open T _C = 110°C V _{DRM} = Max. Rating		I _{DRM}		0.5 [#]	0.5	0.5	mA MAX
Maximum On-State Voltage, (1) at T _C = 25°C and I _T = Rated Amps		V _{TM}		1.6	1.6	1.6	VOLT MAX
DC Holding Current, (1) Gate Open and T _C = 25°C		I _{HO}			50	50	mA MAX
Critical Rate-Of-Rise of Off-State Voltage, (1) for V _D = V _{DRM} Gate Open, T _C = 110°C		dV/dt			50	50	V/μsec.
Critical Rate-Of-Rise of Commutation Voltage, (1) at T _C = 80°C, Gate Unenergized, V _D = V _{DRM} I _T = I _{T(RMS)}		dV/dt		3	4	4	V/μsec.
Gate-Controlled Turn-on Time for V _D = V _{DRM} t _R = 0.1 μsec., I _T = 6A (Peak) and T _C = 25°C		T _{gt}		3	3	3	μsec.
Thermal Resistance, Junction-to-Case		RθJ-C		4.2	3.8	3.4	°C/WATT TYP
TRIGGER DIAC SPECIFICATIONS	Breakover Voltage Symmetry	ΔV _(BO)		3	3	3	Volt
	Breakover Voltage (Forward & Reverse)	V _{BO}		30	30	30	V min
				45	45	45	V max
	Dynamic Breakback Voltage (Forward & Reverse)	[ΔV =]		5	5	5	Volt
	Peak Breakover Current	I _{BO}		200	200	200	μA
Trigger Firing Capacitance	C		0.1	0.1	0.1	μF	

DISCONTINUED

***Notes:**

- (1) All Values Apply in either direction.
- TRIDAC is a registered trademark of Hutson Industries.

